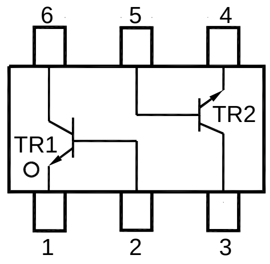
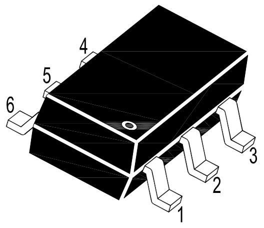
MMBTSC812D

NPN Silicon Epitaxial Planar Transistors

for muting and switching applications.





1. Emitter 2. Base 3. Collector
4. Emitter 5. Base 6. Collector
SOT-26 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V_{EBO}	25	V
Collector Current	I_C	300	mA
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Type	Max.	Unit
DC Current Gain at V_{CE} = 2 V, I_C = 4 mA	h_{FE}	350	-	1200	-
Collector Base Cutoff Current at V_{CB} = 50 V	I_{CBO}	-	-	100	nA
Emitter Base Cutoff Current at V_{EB} = 25 V	I_{EBO}	-	-	100	nA
Collector Emitter Saturation Voltage at I_C = 30 mA, I_B = 3 mA	$V_{CE(sat)}$	-	-	0.3	V
Base Emitter Voltage at I_C = 4 mA, V_{CE} = 2 V	$-V_{BE(on)}$	-	0.61	-	V
Current Gain Bandwidth Product at V_{CE} = 6 V, I_C = 4 mA,	f_T	-	30	-	MHz
Collector Output Capacitance at V_{CB} = 10 V, I_E = 0, f = 1 MHz	C_{ob}	-	-	7	pF

®

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ISO/TS 16949 : 2009 Certificate No. 05103
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IECQ QC 080000 Certificate No. PRC-HSPM-1483-1

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